

## Direct Dark Matter search with the CRESST-III experiment Status and prospects

Alpine Particle Physics Symposium: Dark Matter

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Cryogenic **Rare Event Search** with Superconducting Thermometers



https://cresst-experiment.org

## **CRESST** collaboration

### ~60 people from 8 institutions from 5 countries in Europe

TÜBINGEN



### June 2023, CRESST collaboration meeting in Bratislava







## The CRESST experiment searches for sub-GeV DM particles.

### Interaction:



### Expected differential energy spectrum in CaWO4





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# Small energy deposition in the crystal leads to a measurable TES resistance change.



Target: various crystal materials (CaWO<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, LiAlO<sub>2</sub>, Si) Sensor: W-TES at 15 mK



### Small energy deposition in the crystal leads to a measurable TES resistance change. **Detector:**





## Additional light signal allows to discriminate electron and nuclear recoils to reduce background signal.





## part of the deposited energy is released as *light*.



ALPS 2024 | April 1-6 2024 | Johannes Rothe

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**CRESST-III** detector module



For scintillating target materials (e.g.CaWO<sub>4</sub>), a small part of the deposited energy is released as *light*.



## The CRESST experiment is located in the deep underground laboratory LNGS in Italy that provides excellent shielding against cosmic radiation.







Muon flux: 3•10<sup>-8</sup>/(cm<sup>2</sup> s) Neutrons: 4•10<sup>-6</sup>/(cm<sup>2</sup> s)





# First results from CRESST-III (2019): leading limit for sub-GeV DM with a **30 eV** energy threshold detector.





## Sharply rising energy spectrum below 200 eV - low energy excess (LEE) is observed in CRESST-III detectors and limits the sensitivity to sub-GeV DM.









# Sharply rising energy spectrum below 200 eV - **low energy excess (LEE)** - is observed in CRESST-III detectors and limits the sensitivity to sub-GeV DM.





## Multiple design modifications were applied in the most-recent data-taking campaign to test ideas about the LEE origin.



CaWO<sub>4</sub> grown at TUM



Commercially grown CaWO<sub>4</sub>





 $Al_2O_3$ 

Si

### **Recent measurement campaign started in November 2020 and was completed in February 2024.**

- Various target materials: CaWO<sub>4</sub>, Al<sub>2</sub>O<sub>3</sub>, LiAlO<sub>2</sub>, Si
- Different holding structures (sticks, clamps)
- Remove scintillating parts (foil, sticks, scintillating crystals)







### All thresholds are at O(10 eV) LEE is observed in all detectors

## LEE rate is decaying with time. Excess rate increases after warming up the cryostat to O(10K).



Rate increase after warmups excludes external and internal radioactivity as well as DM as a major origin of the LEE. For all detectors, **spectral shape above 40 eV**:

- is well described by a single power law
- has two time components.



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Origins under investigation:
Sensor related events
Relaxation of holding-induced stress
Intrinsic crystal effects

Observation of a mono-energetic nuclear recoil peak at **112 eV** in three CRESST-III CaWO<sub>4</sub> detectors -> new calibration technique



 $\rightarrow$  mono-energetic nuclear recoil Proposed as a low-energy calibration method for cryogenic

L. Thulliez et al 2021 JINST 16 P07032 /

Observation of the nuclear recoil peaks around the predicted 2. provides a potential for **precise energy calibration for nuclear** 

## DM results with different target materials



## Well performing LiAIO, detector allowed to greatly improve the limits for **spin-dependent** DM-nucleon interactions.



**CRESST** technique allows to use various target materials to test different interaction channels!

**Li1 detector**: 10.5 g LiAlO2 Data-taking period: Feb 2021 – Aug 2021

Exposure: 1.161 kg  $\cdot$  days Energy threshold: 83.6 eV

Proton





Neutron

## Si wafer detector: energy threshold of 10 eV extends sensitivity to DM particles with the mass down to 115 MeV/c<sup>2</sup>.

**Si wafer detector**: 0.35 g Data-taking period: Nov 2020 – Aug 2021 Exposure: 55.06 g · days Energy threshold: **10.0 eV** 

Thin wafer detector is a target Bulky detector is a veto to remove coincidence events.

10.0±0.2 eV energy threshold







### Silicon-on-sapphire wafer detector achieves an energy threshold < 10 eV and reaches sensitivity to DM mass < 100 MeV/c<sup>2</sup>.





Al<sub>2</sub>O<sub>3</sub> wafer detector: 0.6 g

## Future: New CRESST detectors



## **Detectors with new module designs to study the LEE origin** are installed at LNGS since February 2024. Taking new data since last week!

Holding structures instrumented holder: target crystal only touches other cryodetectors 4 pi veto: target crystal surrounded by silicon beaker

 $\rightarrow$ discriminate external events and events transmitted through the holding structure





**Double TES read-out**  $\rightarrow$  discriminate events in the absorber from events in the TES films or material interfaces  $\rightarrow$  stress-free holding scheme: reduced thermal stress on target crystals



4cm<sup>2</sup> silicon-on-sapphire



4cm<sup>3</sup> CaWO<sub>4</sub>

### Talk by Francesca Pucci at EXCESS23@TAUP

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TES1 TES2



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### Silicon-on-sapphire double-TES



20x20x0.4mm<sup>3</sup> wafer operated above ground at MPP thresholds of 27 eV & 20.5 eV (5 $\sigma$ ) two 55Fe sources reveal mild position-dependence

At low energy: band of coincident events + distributions of single-TES events

 $\rightarrow$  low-background operation at LNGS started!



published on arXiv today: 2404.02607



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55 Fe

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## Above-ground measurements with double-TES detectors show potential to Pulse shapes:

### Silicon-on-sapphire double-TES



 $20x20x0.4mm^3$  wafer operated above ground at MPP thresholds of 27 eV & 20.5 eV (5 $\sigma$ ) two 55Fe sources reveal mild position-dependence

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## **Conclusions & Outlook**



CRESS

A major CRESST setup upgrade to 288 read-out channels is in

- new DAQ and bias electronics
- goal: installation at LNGS in

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## Thank you for your attention!





keV

### CaWO<sub>4</sub> double-TES



24g crystal operated at MPP thresholds of 137 eV & 148 eV (5 $\sigma$ ) e 2x 55Fe sources reveal mild position-dependence

At low energy: band of coincident events + distributions of single-TES events

Resolution limited by high rate above-ground  $\rightarrow$  low-threshold operation at LNGS starting soon

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